

GaP, wurtzite modification: energy gap

Semiconductors - New Data and Updates for several III-V (including mixed crystals) and II-VI Compounds

substance:	gallium phosphide (GaP), wurtzite modification
property:	energy gap (electronic properties)

energy gap

The theoretical value of the direct gap in the wurtzite phase between the Γ_{9v} valence-band maximum and the Γ_{8c} conduction-band minimum is 2.251 eV, as determined by empirical pseudopotential calculations including spin-orbit coupling [[10D](#)].

References

10D De, A., Pryor, E.: Phys. Rev. B **81** (2010) 155210.